



SEMITOP[®] 2

IGBT Module

SK10GH123

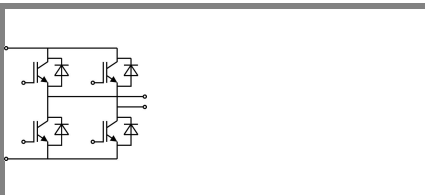
Preliminary Data

Features

- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- N-channel homogeneous silicon structure (NPT-Non punch-through IGBT)
- High short circuit capability
- Low tail current with low temperature dependence
- UL recognized, file no. E63532

Typical Applications

- Switching (not for linear use)
- Inverter
- Switched mode power supplies
- UPS



GH

Absolute Maximum Ratings		$T_s = 25\text{ °C}$, unless otherwise specified			
Symbol	Conditions	Values			Units
IGBT					
V_{CES}	$T_j = 25\text{ °C}$	1200			V
I_C	$T_j = 125\text{ °C}$	$T_s = 25\text{ °C}$	16		A
		$T_s = 80\text{ °C}$	11		A
I_{CRM}	$I_{CRM} = 2 \times I_{Cnom}$	16			A
V_{GES}		± 20			V
t_{psc}	$V_{CC} = 600\text{ V}; V_{GE} \leq 20\text{ V}; T_j = 125\text{ °C}$ $V_{CES} < 1200\text{ V}$	10			μs
Inverse Diode					
I_F	$T_j = 150\text{ °C}$	$T_s = 25\text{ °C}$	18		A
		$T_s = 80\text{ °C}$	12		A
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$				A
I_{FSM}	$t_p = 10\text{ ms}; \text{half sine wave } T_j = 150\text{ °C}$	125			A
Module					
$I_{t(RMS)}$					A
T_{vj}		-40 ... +150			$^{\circ}\text{C}$
T_{stg}		-40 ... +125			$^{\circ}\text{C}$
V_{isol}	AC, 1 min.	2500			V

Characteristics		$T_s = 25\text{ °C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 0,35\text{ mA}$	4,5	5,5	6,5	V
I_{CES}	$V_{GE} = 0\text{ V}, V_{CE} = V_{CES}$	$T_j = 25\text{ °C}$	0,05		mA
		$T_j = 125\text{ °C}$			mA
I_{GES}	$V_{CE} = 0\text{ V}, V_{GE} = 30\text{ V}$	$T_j = 25\text{ °C}$	120		nA
		$T_j = 125\text{ °C}$			nA
V_{CE0}		$T_j = 25\text{ °C}$	1,2		V
		$T_j = 125\text{ °C}$	1,2		V
r_{CE}	$V_{GE} = 15\text{ V}$	$T_j = 25\text{ °C}$	150		$\text{m}\Omega$
		$T_j = 125\text{ °C}$	210		$\text{m}\Omega$
$V_{CE(sat)}$	$I_{Cnom} = 10\text{ A}, V_{GE} = 15\text{ V}$	$T_j = 25\text{ °C}_{\text{chiplev.}}$	2,7	3,2	V
		$T_j = 125\text{ °C}_{\text{chiplev.}}$	3,3	3,9	V
C_{ies}	$V_{CE} = 25, V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	0,6		nF
C_{oes}			0,06		nF
C_{res}			0,038		nF
$t_{d(on)}$	$R_{Gon} = 50\ \Omega$	$V_{CC} = 600\text{ V}$ $I_C = 10\text{ A}$	30		ns
t_r			45		ns
E_{on}	$R_{Goff} = 50\ \Omega$	$T_j = 125\text{ °C}$ $V_{GE} = \pm 15\text{ V}$	1,3		mJ
$t_{d(off)}$			200		ns
t_f			35		ns
E_{off}			1		mJ
$R_{th(j-s)}$	per IGBT	1,8			K/W



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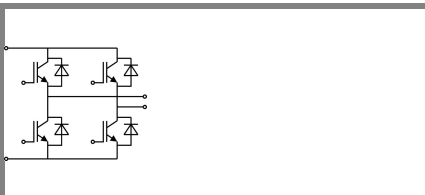
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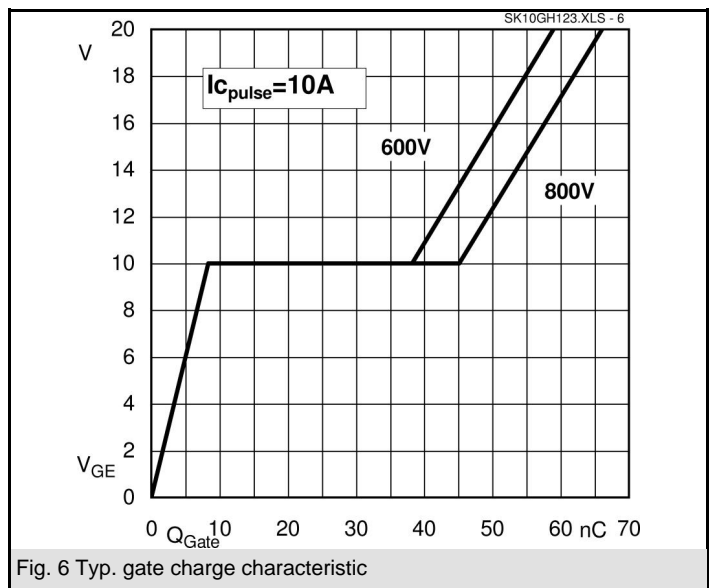
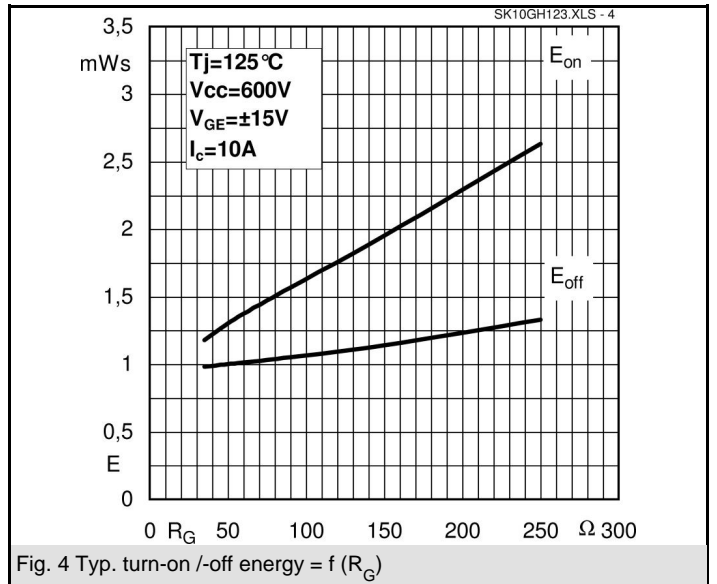
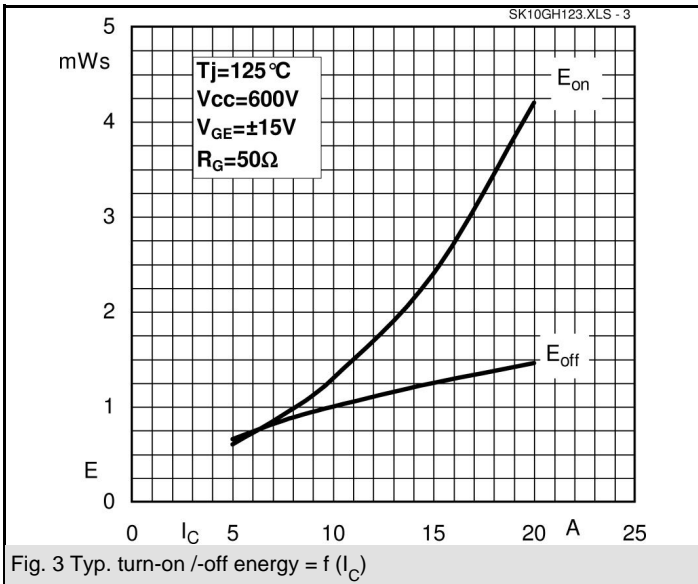
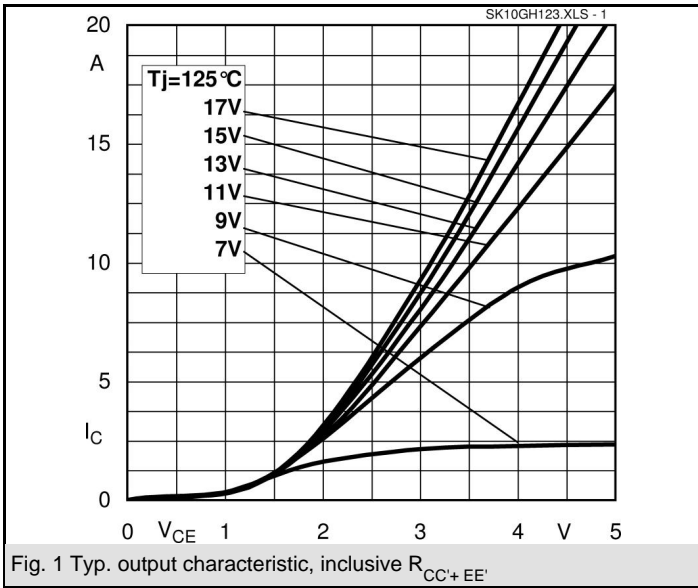
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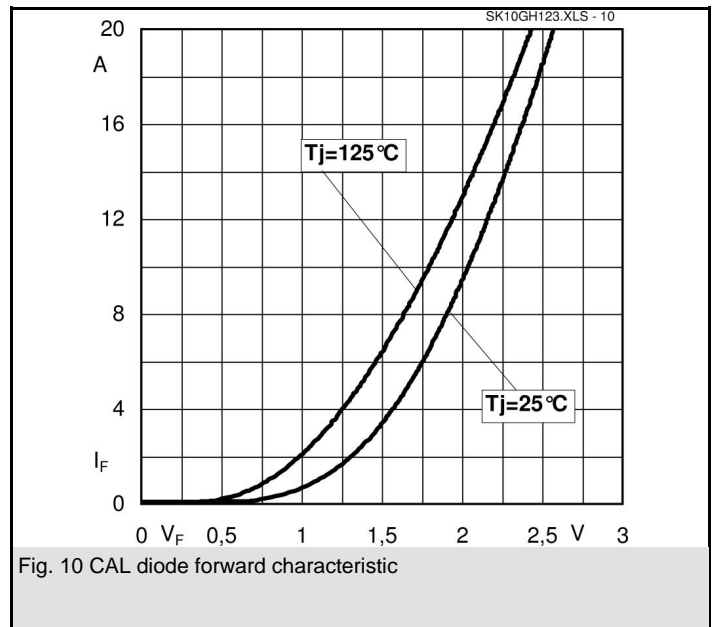
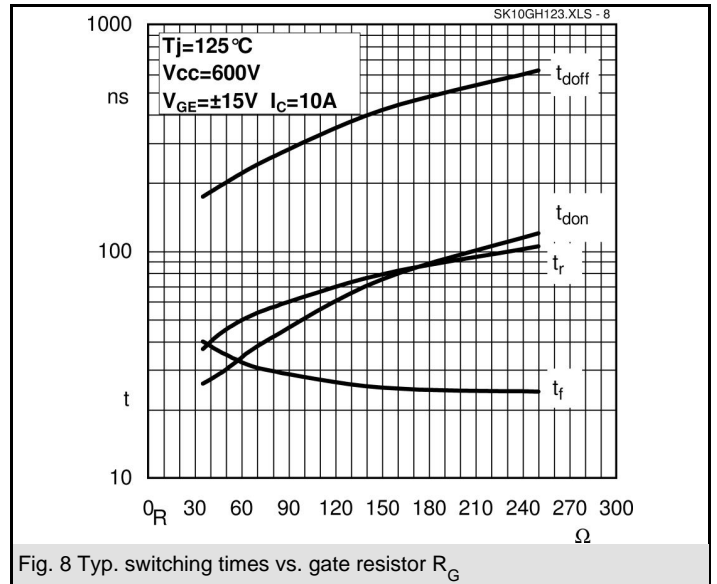
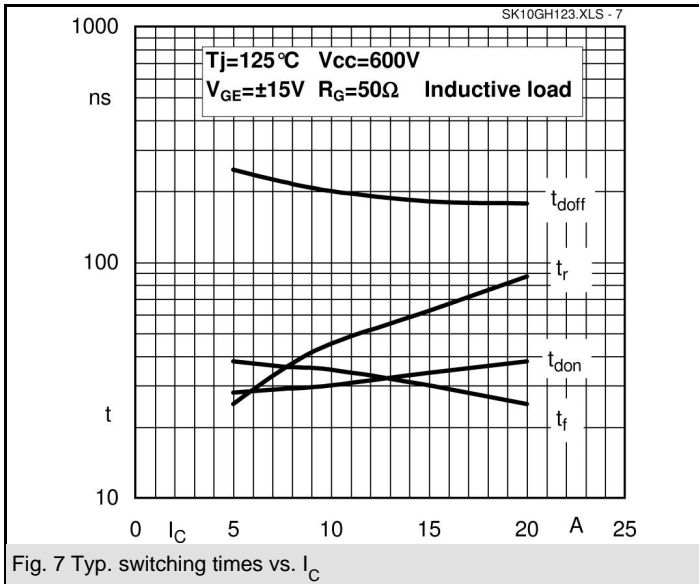
Characteristics

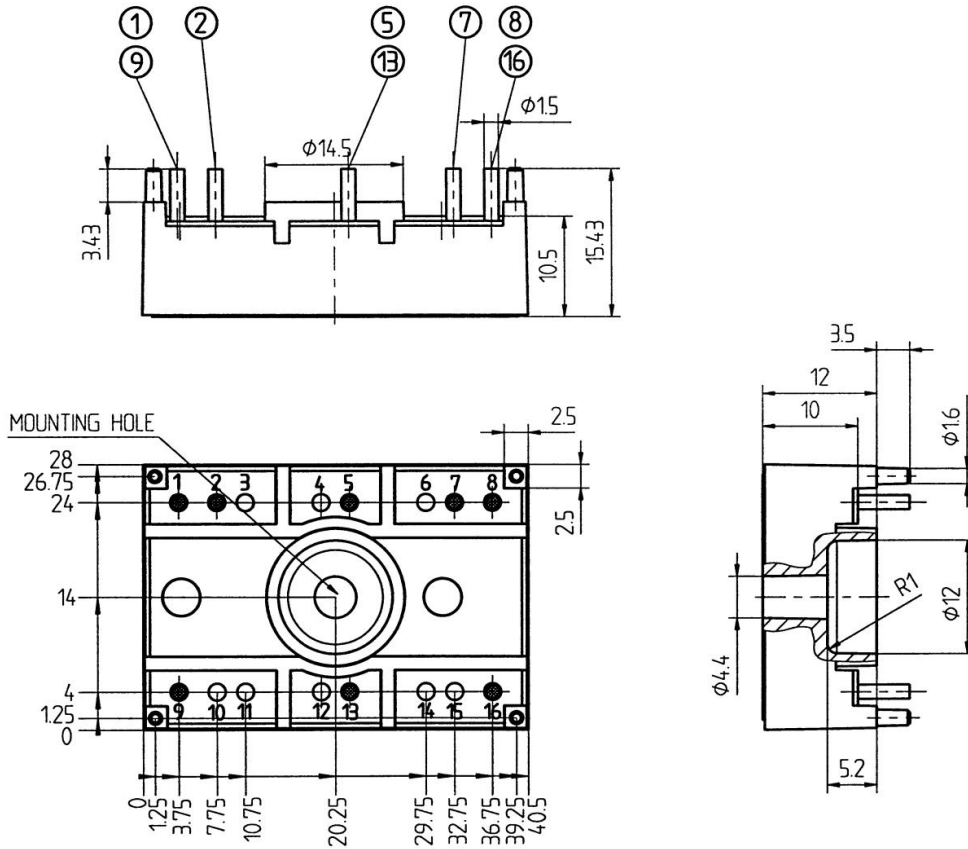
Symbol	Conditions	min.	typ.	max.	Units
Inverse Diode					
$V_F = V_{EC}$	$I_{Fnom} = 10 \text{ A}; V_{GE} = 0 \text{ V}$		2	2,5	V
			1,8	2,3	V
V_{F0}			1	1,2	V
r_F			80	110	mΩ
I_{RRM}	$I_F = 10 \text{ A}$		12		A
Q_{rr}	$di/dt = -300 \text{ A}/\mu\text{s}$		1,8		μC
E_{rr}	$V_{CC} = 600 \text{ V}$		0,4		mJ
$R_{th(j-s)D}$	per diode			2,1	K/W
M_s	to heat sink M1			2	Nm
w			21		g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.







Case T5 (Suggested hole diameter, in the PCB, for solder pins and plastic mounting pins: 2mm)

